

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# XPN9R614MC

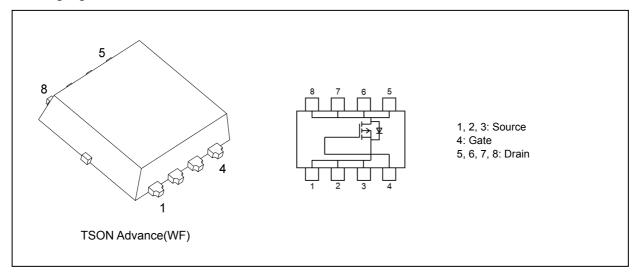
### 1. Applications

- · Automotive
- Switching Voltage Regulators
- · DC-DC Converters
- · Motor Drivers

#### 2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 7.4 \text{ m}\Omega$  (typ.) ( $V_{GS} = -10 \text{ V}$ )
- (4) Low leakage current:  $I_{DSS} = -10 \mu A (max) (V_{DS} = -40 V)$
- (5) Enhancement mode:  $V_{th}$  = -1.0 to -2.1 V ( $V_{DS}$  = -10 V,  $I_D$  = -0.5 mA)

### 3. Packaging and Internal Circuit



1



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Character	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	-40	V
Gate-source voltage			V <sub>GSS</sub>	+10/-20	
Drain current (DC)		(Note 1)	I <sub>D</sub>	-40	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	-80	
Power dissipation	(T <sub>c</sub> = 25 °C)		P <sub>D</sub>	100	W
Power dissipation	(t = 10 s)	(Note 2)		2.27	]
Power dissipation	(t = 10 s)	(Note 3)		0.84	Ī
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	67	mJ
Single-pulse avalanche current			I <sub>AS</sub>	-40	Α
Channel temperature		(Note 5)	T <sub>ch</sub>	175	°C
Storage temperature		(Note 5)	T <sub>stg</sub>	-55 to 175	

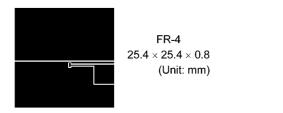
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

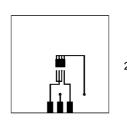
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal impedance	(T <sub>c</sub> = 25 °C)		Z <sub>th(ch-c)</sub>	1.5	°C/W
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 2)	Z <sub>th(ch-a)</sub>	66	
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 3)	Z <sub>th(ch-a)</sub>	178	

- Note 1: Ensure that the channel temperature does not exceed 175 °C.
- Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
- Note 4:  $V_{DD}$  = -25 V,  $T_{ch}$  = 25 °C (initial), L = 43  $\mu$ H,  $R_{G}$  = 25  $\Omega$ ,  $I_{AS}$  = -40 A,  $V_{GS}$  = 0/-15 V
- Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.





FR-4  $25.4 \times 25.4 \times 0.8$  (Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = +10/-20 V, V <sub>DS</sub> = 0 V	_	_	±1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = -40 V, V <sub>GS</sub> = 0 V	_		-10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-40			V
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 10 V	-30			
Gate threshold voltage	$V_{th}$	$V_{DS} = -10 \text{ V}, I_{D} = -0.5 \text{ mA}$	-1.0		-2.1	
Drain-source on-resistance	R <sub>DS(ON)</sub>	$V_{GS}$ = -4.5 V, $I_D$ = -20 A	_	9.6	13.4	mΩ
		$V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	_	7.4	9.6	

## 6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	3000	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	335	_	
Output capacitance	C <sub>oss</sub>		_	410		
Gate resistance	r <sub>g</sub>		_	13		Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	35	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	50		
Switching time (fall time)	t <sub>f</sub>		_	165	_	
Switching time (turn-off time)	t <sub>off</sub>		_	570	1	

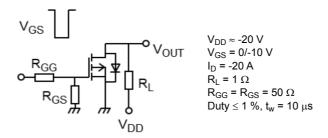


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx -32 \text{ V}, V_{GS} = -10 \text{ V},$ $I_{D} = -40 \text{ A}$	_	64		nC
Gate-source charge 1	Q <sub>gs1</sub>		_	8		
Gate-drain charge	$Q_{gd}$		_	17	_	

## 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

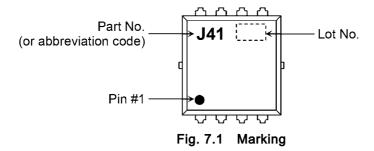
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 6)	I <sub>DR</sub>	_	_	_	-40	Α
Reverse drain current (pulsed)	(Note 6)	I <sub>DRP</sub>	_	_	_	-80	Α
Diode forward voltage		$V_{DSF}$	$I_{DR} = -40 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V

Note 6: Ensure that the channel temperature does not exceed 175 °C.

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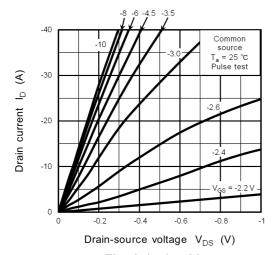


## 7. Marking





### 8. Characteristics Curves (Note)





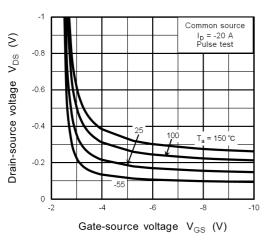


Fig. 8.3 V<sub>DS</sub> - V<sub>GS</sub>

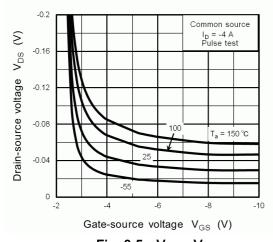


Fig. 8.5  $V_{DS}$  -  $V_{GS}$ 

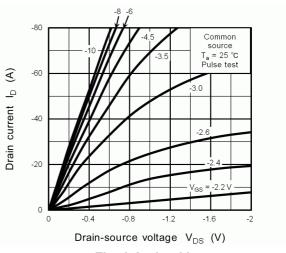


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

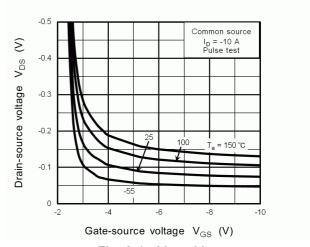


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

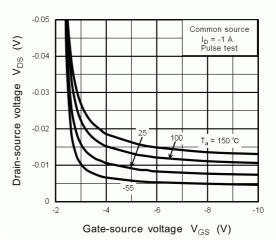


Fig. 8.6 V<sub>DS</sub> - V<sub>GS</sub>



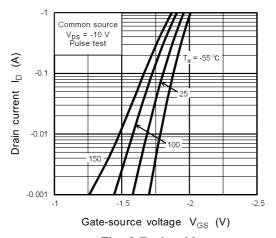


Fig. 8.7  $I_D - V_{GS}$ 

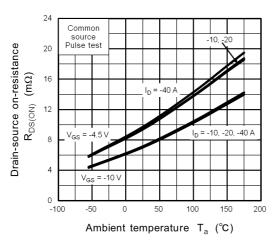


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

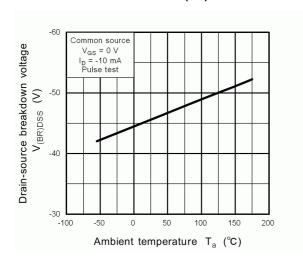


Fig. 8.11 V<sub>(BR)DSS</sub> - T<sub>a</sub>

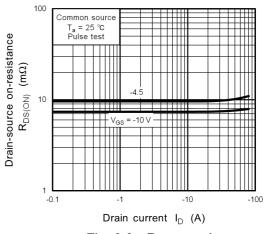


Fig. 8.8 R<sub>DS(ON)</sub> - I<sub>D</sub>

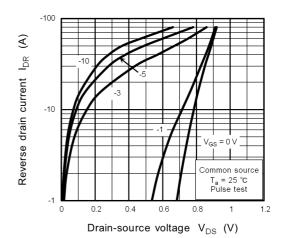


Fig. 8.10 IDR - VDS

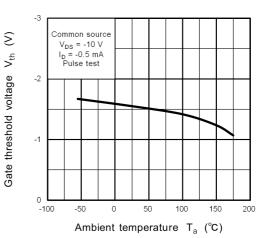
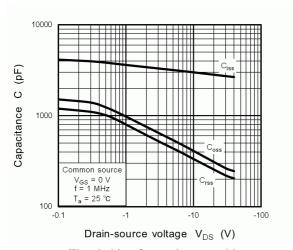


Fig. 8.12 V<sub>th</sub> - T<sub>a</sub>







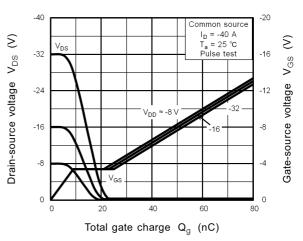


Fig. 8.14 Dynamic Input/Output Characteristics



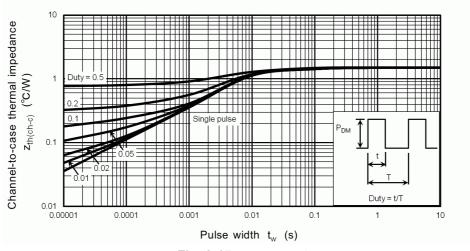
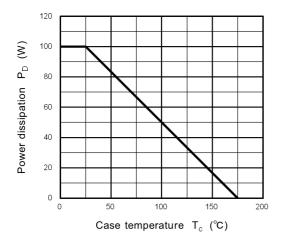


Fig. 8.15  $z_{th(ch-c)} - t_w$  (Guaranteed Maximum)



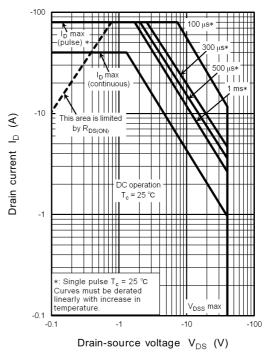


Fig. 8.16 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

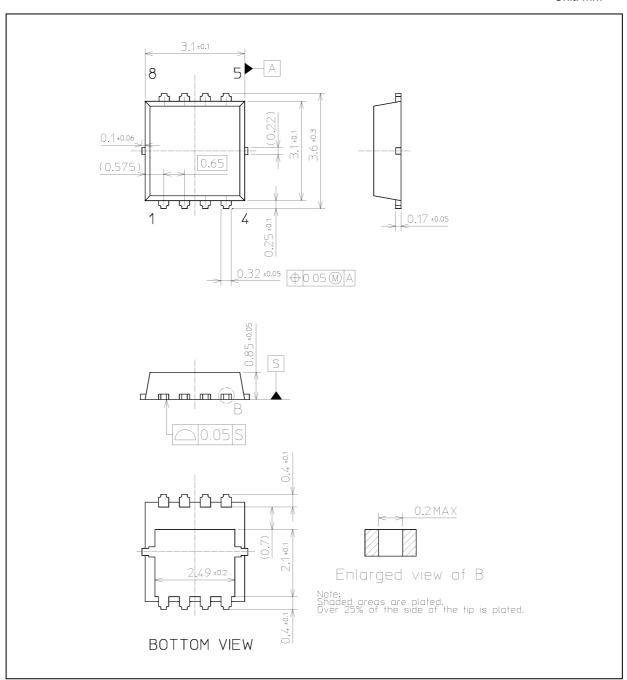
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.029 g (typ.)

Package Name(s)			
TOSHIBA: 2-3X2A			
Nickname: TSON Advance(WF)			



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